

TOSHIBA Photo-Interrupter Infrared LED + Phototransistor

TLP833(F)

Lead Free Product

Copiers, Printers, Fax Machines

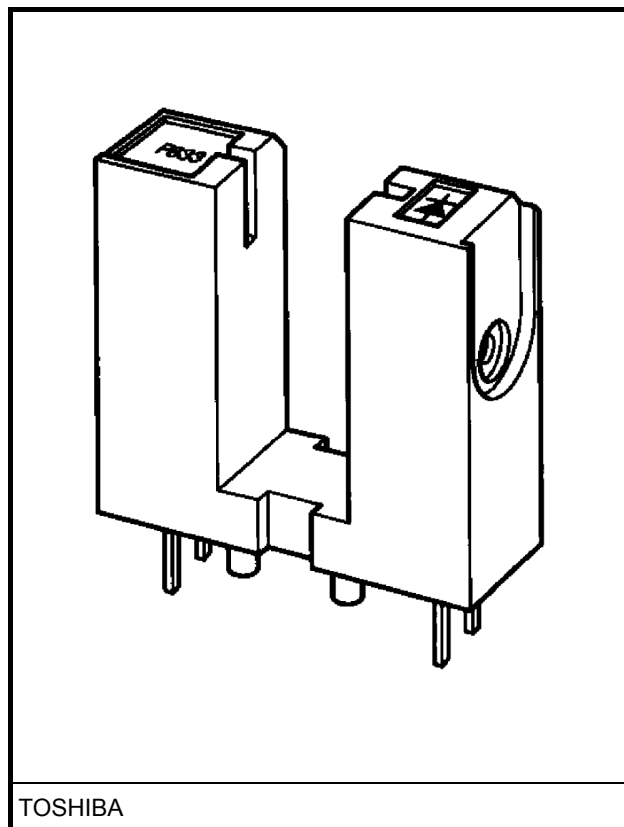
VCRS, Microwave Ovens, Air Conditioners

Automatic Vending Machines

Various Position Detection Sensors

The TLP833(F) is a photo-interrupter which incorporates a high radiant power GaAs LED and a fast-response Si photo-transistor. The package has a deep gap.

- Package with deep gap (gap: 12 mm)
- Designed for direct mounting on printed circuit boards (positioning pins included).
- Gap: 5mm
- Resolution: Slit width 0.5mm
- High current transfer ratio: $I_C/I_F = 5\%$ (min)
- High temperature operation: $T_{opr} = 95^\circ\text{C}$ (max)
- Package material: Polybutylene terephthalate (UL94-V-0)
- Detector impermeable to visible light

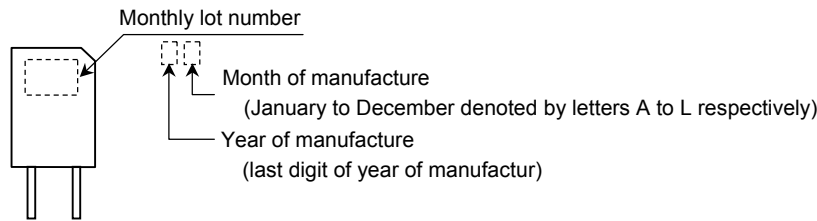


Weight: 1g (typ.)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic			Symbol	Rating	Unit
LED	Forward current		I _F	50	mA
	Forward current derating	25°C < T _a ≤ 85°C	ΔI _F /°C	−0.33	mA/°C
		T _a > 85°C		−2	
	Reverse voltage		V _R	5	V
Detector	Collector–emitter voltage		V _{CEO}	35	V
	Emitter–collector voltage		V _{ECO}	5	V
	Collector power dissipation		P _C	75	mW
	Collector power dissipation derating (T _a > 25°C)		ΔP _C /°C	−1	mW/°C
Collector current			I _C	50	mA
Operating temperature range			T _{opr}	−30~85	°C
Storage temperature range			T _{stg}	−40~100	°C
Soldering temperature (5 s)			T _{sol}	260	°C

Markings



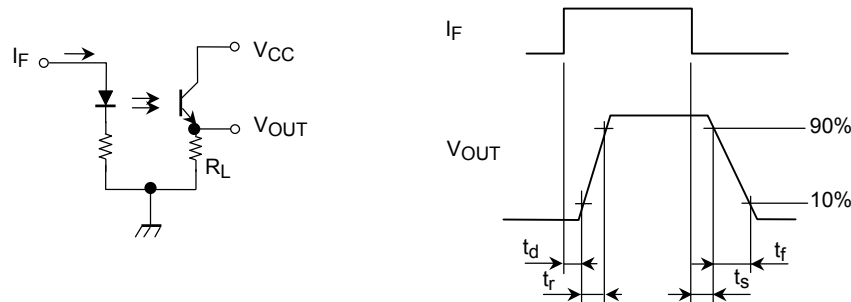
Recommended Operating Conditions

Characteristic	Symbol	Min	Typ.	Max	Unit
Supply voltage	V_{CC}	—	5	24	V
Forward current	I_F	—	—	25	mA
Operating temperature	T_{opr}	-10	—	75	°C

Optical Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
LED	Forward voltage	V_F	$I_F = 10\text{mA}$	1.00	1.15	1.30	V
	Reverse current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Peak emission wavelength	λ_P	$I_F = 10\text{mA}$	—	940	—	nm
Detector	Dark current	$I_D (I_{CEO})$	$V_{CE} = 24\text{V}, I_F = 0$	—	—	0.1	μA
	Peak sensitivity wavelength	λ_P	—	—	870	—	nm
Coupled	Current transfer ratio	I_C/I_F	$V_{CE} = 2\text{V}, I_F = 10\text{mA}$	5	—	100	%
	Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_F = 20\text{mA}, I_C = 0.5\text{mA}$	—	0.1	0.35	V
	Rise time	t_r	$V_{CC} = 5\text{V}, I_C = 1\text{mA}$ $R_L = 1\text{k}\Omega$ (Note)	—	15	—	μs
	Fall time	t_f		—	15	—	

(Note): Switching time measurement circuit and waveform



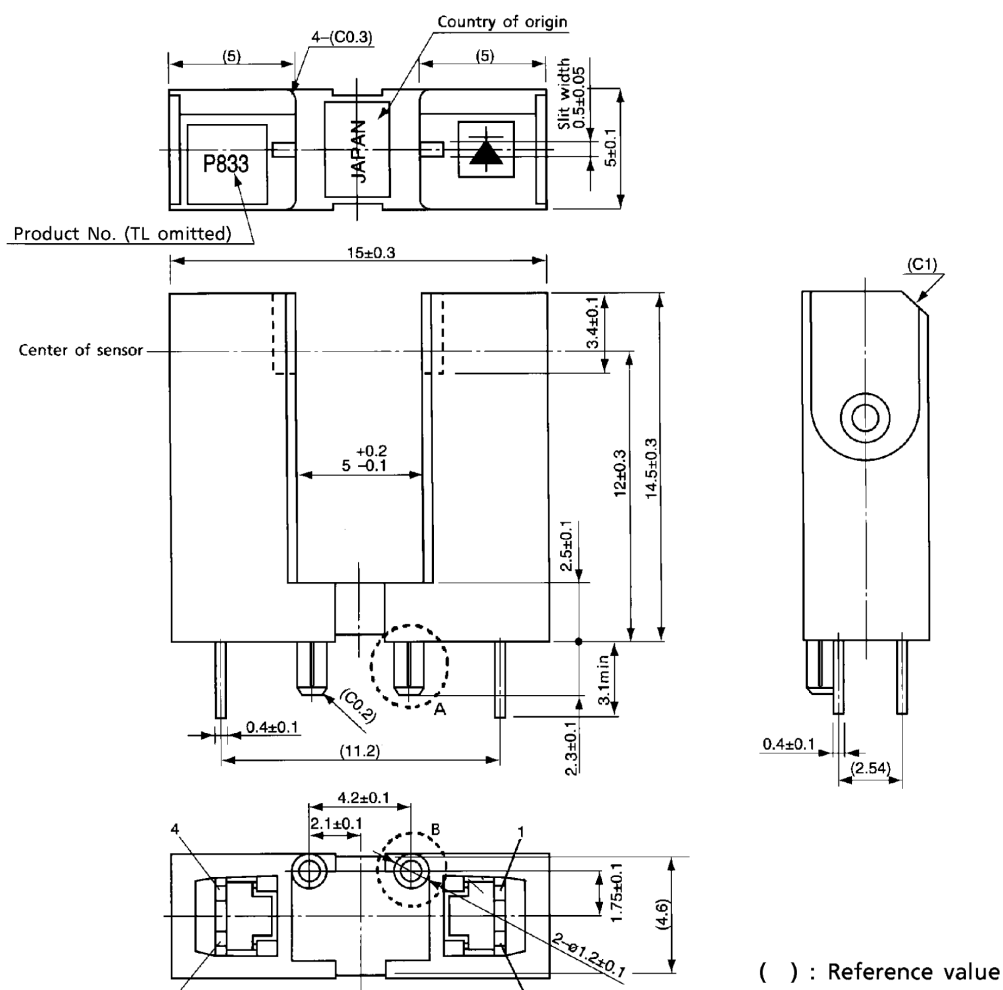
Precautions

1. Clean only the soldered part of the leads. Do not immerse the entire package in the cleaning solvent.
2. The package is made of polybutylene-terephthalate. Oil or chemicals may cause the package to melt or crack. Care must be taken in relation to the environment in which the device is to be installed.
3. Mount the device on a level surface.
4. Keep the device away from external light. Although the phototransistor is of low optical sensitivity, the device may malfunction if external light with a wavelength of 700 nm or more is allowed to impinge on it.
5. Conversion efficiency falls over time due to the current which flows in the infrared LED. When designing a circuit, take into account this change in conversion efficiency over time.
The ratio of fluctuation in conversion efficiency to fluctuation in infrared LED optical output is 1 : 1.

$$\frac{I_C/I_F(t)}{I_C/I_F(0)} = \frac{P_O(t)}{P_O(0)}$$

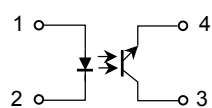
Package Dimensions

Unit: mm



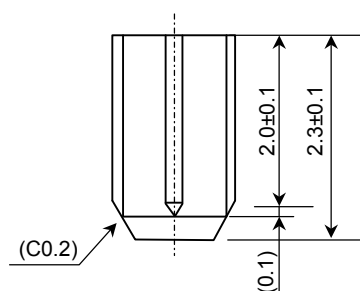
Weight: 1 g (typ.)

Pin Connection

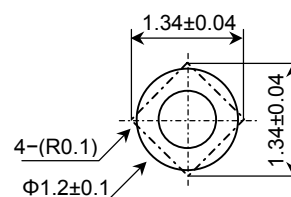


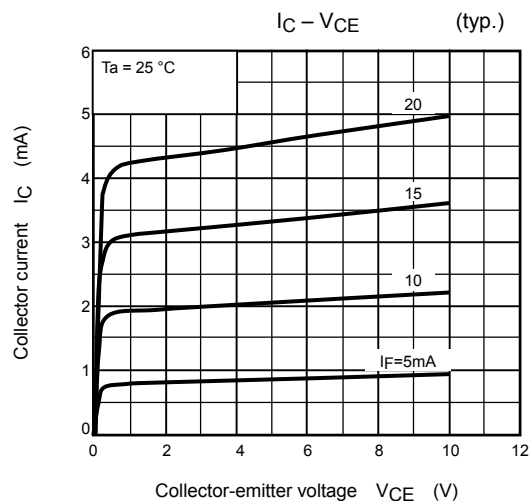
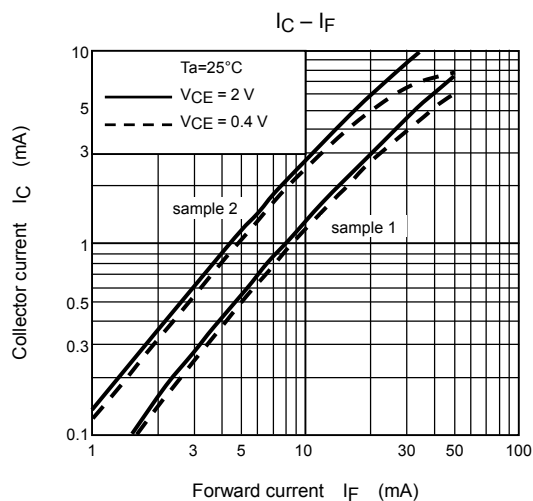
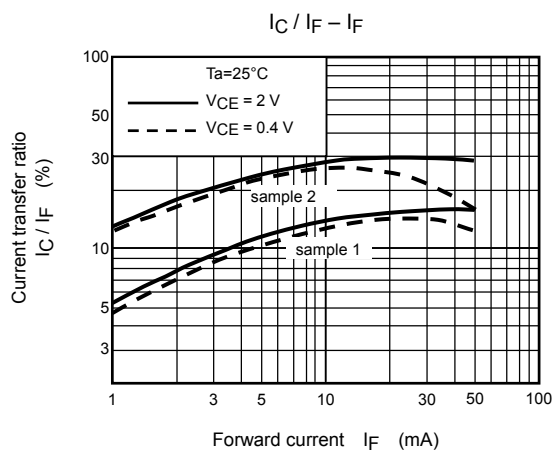
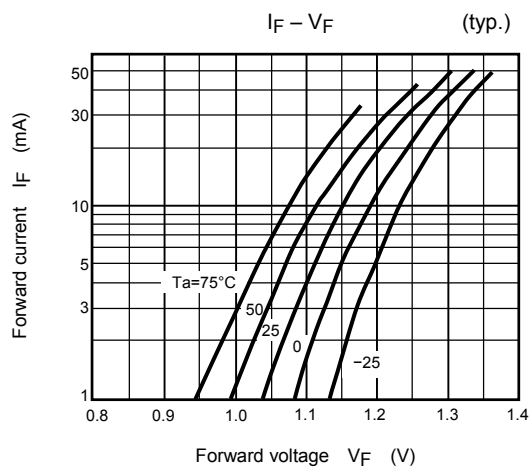
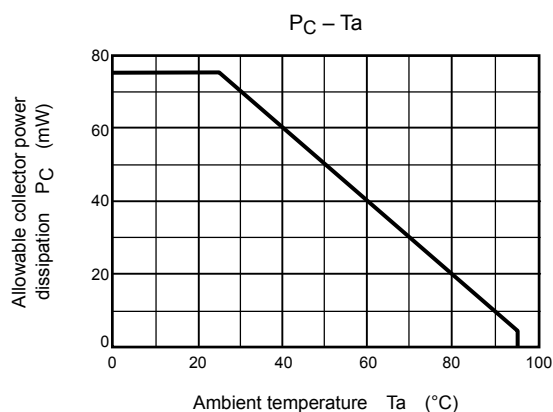
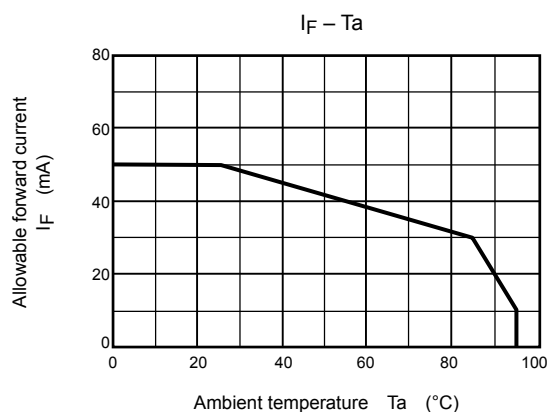
1. Anode
2. Cathode
3. Collector
4. Emitter

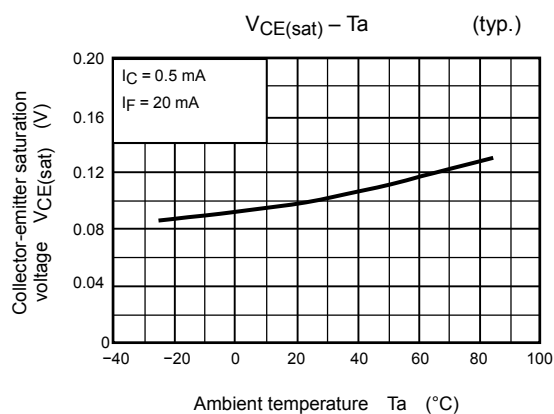
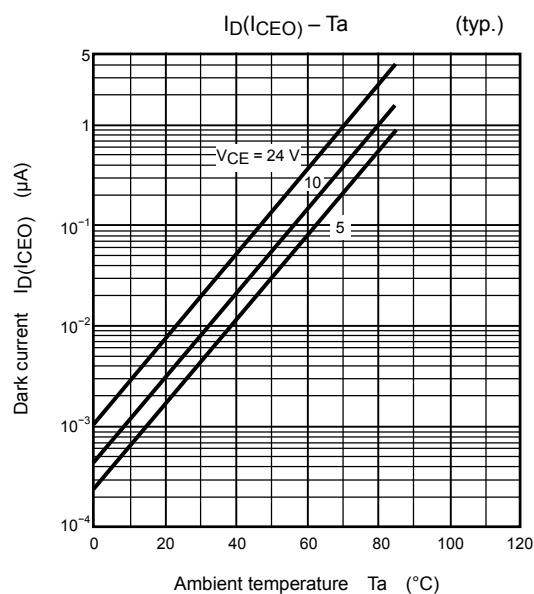
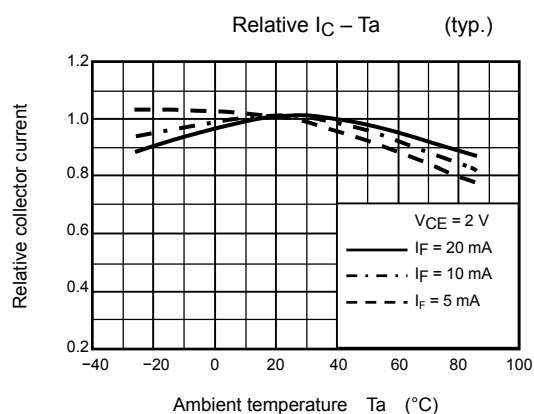
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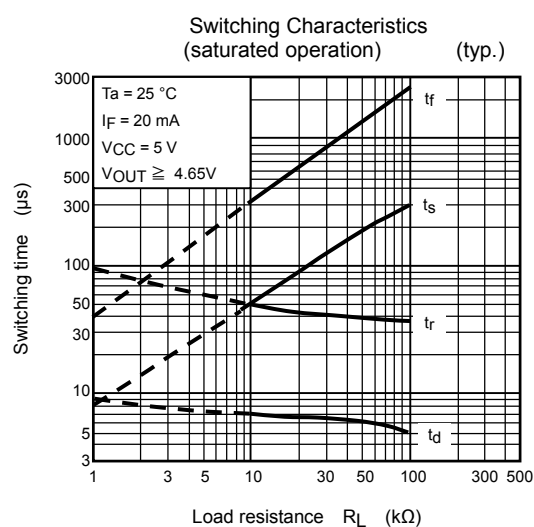
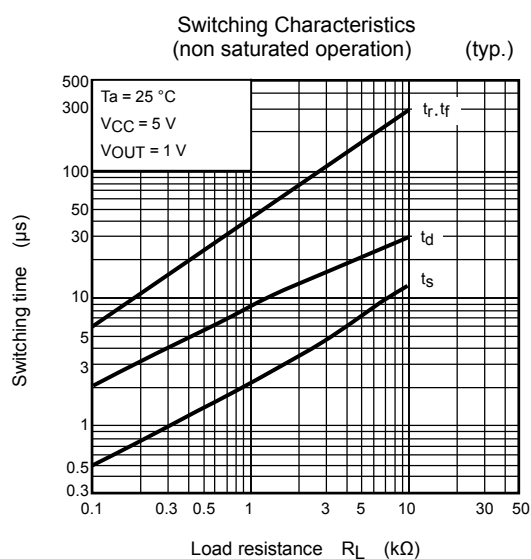
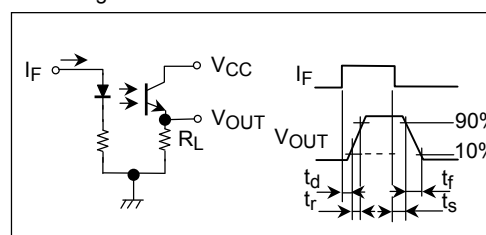
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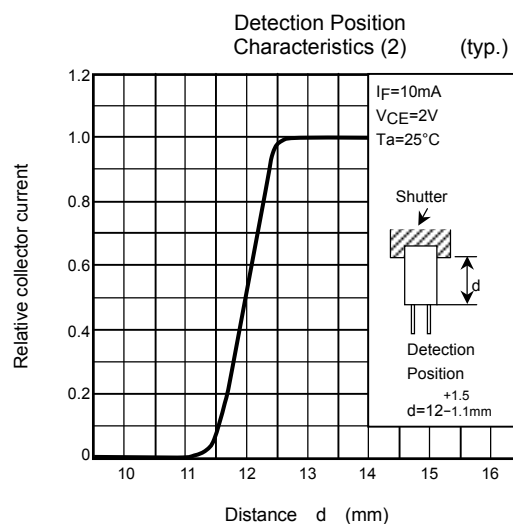
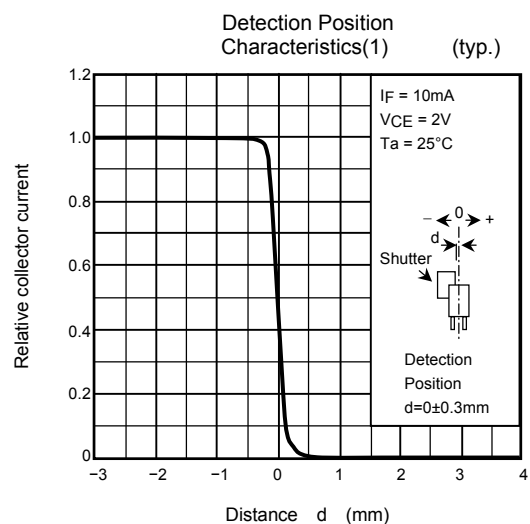






Switching Time Test Circuit





Relative Positioning Of Shutter And Device

For normal operation position the shutter and the device as shown in the figure below. By considering the device's detection direction characteristic and switching time, determine the shutter slit width and pitch.

